N-channel 40 V, 1.3 mΩ logic level MOSFET in LFPAK56
31 May 2018 Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- · Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower $R_{\mbox{\scriptsize DSon}}$ in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - · Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced R_{th} and R_{DSon}
 - · Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- · Motors, lamps and solenoid control
- · Start-Stop micro-hybrid applications
- · Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	190	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	395	W



Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; Fig. 11		0.67	0.96	1.3	mΩ	
Dynamic chara	acteristics							
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 4.5 V; Fig. 13; Fig. 14		-	11.2	22.4	nC	
Source-drain diode								
Q _r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; <u>Fig. 17</u>		-	38.8	-	nC	
S	softness factor			-	0.8	-		

^{[1] 190}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

5. Pinning information

Table 2. Pinning information

Table 2.1 Illining information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	S	source	mb	D			
2	S	source					
3	S	source	q	G T			
4	G	gate		mbb076 S			
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)				

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Y1R3-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y1R3-40H	91H340

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

BUK9Y1R3-40H

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Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	16	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	395	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	190	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	190	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	600	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode		'			
I _S	source current	T _{mb} = 25 °C	[2]	-	145	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	600	Α
Avalanche r	uggedness			-	1	,
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 190 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	154	mJ

- [1] 190A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature
- [2] 145A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}$ C.
- [4] Refer to application note AN10273 for further information.

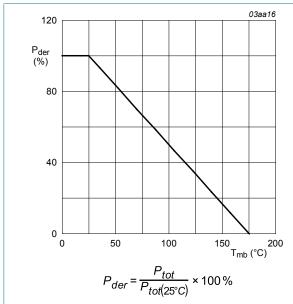
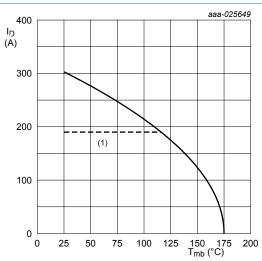


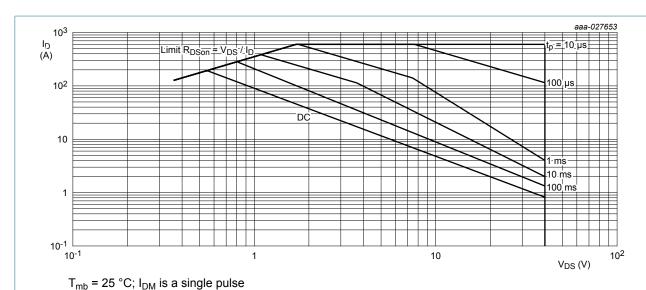
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



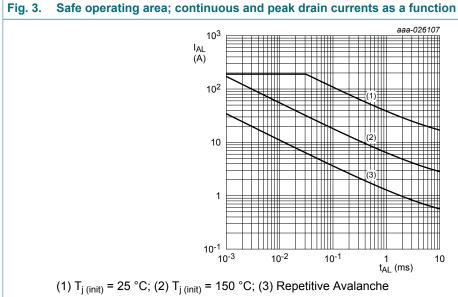
 $V_{GS} \ge 10 \text{ V}$

(1) 190A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature



Safe operating area; continuous and peak drain currents as a function of drain-source voltage



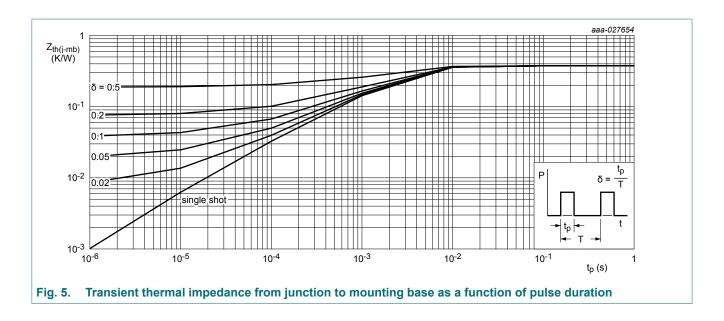
Avalanche rating; avalanche current as a function of avalanche time Fig. 4.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	0.29	0.38	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			_
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	43	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 ^{\circ} C$	-	40.5	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9; Fig. 10}$	1.35	1.62	2.05	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.6	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.4	1	μΑ
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	2.4	10	μΑ
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	0.34	1	mA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	0.67	0.96	1.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 12	1	1.47	2.1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 12	1.1	1.6	2.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12	1.4	2.04	2.8	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 11	0.85	1.21	1.8	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 105 °C; Fig. 12	1.26	1.82	2.8	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 125 °C; Fig. 12	1.4	1.97	3.1	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 175 °C; Fig. 12	1.76	2.5	3.9	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.58	1.46	3.65	mΩ
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V; Fig. 13; Fig. 14	-	99	139	nC
		I _D = 25 A; V _{DS} = 20 V; V _{GS} = 4.5 V; Fig. 13; Fig. 14	-	45.3	63.4	nC
Q _{GS}	gate-source charge		-	16.1	24.2	nC
Q _{GD}	gate-drain charge		-	11.2	22.4	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	6978	9769	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	1244	1742	pF
C _{rss}	reverse transfer capacitance		-	269	592	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 4.5 \text{ V};$	-	36.3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	42.5	-	ns
t _{d(off)}	turn-off delay time	1	-	51.8	-	ns
t _f	fall time	1	-	30.7	-	ns
Source-dra	in diode		<u> </u>			
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	38.7	-	ns
Q _r	recovered charge	V _{DS} = 20 V; T _j = 25 °C; <u>Fig. 17</u>	-	38.8	-	nC
S	softness factor	†	-	0.8	-	+
		I_S = 25 A; dI_S/dt = -500 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_i = 25 °C; Fig. 17	-	0.72	-	

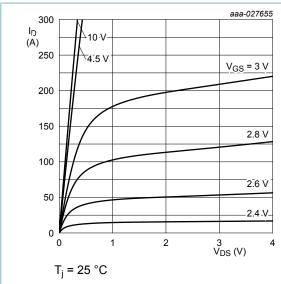


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

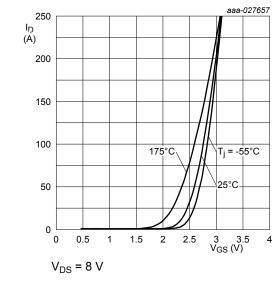


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

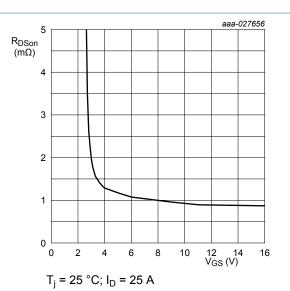


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

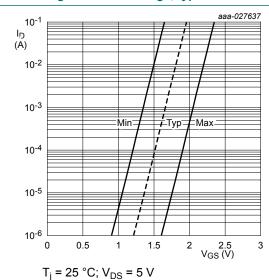


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

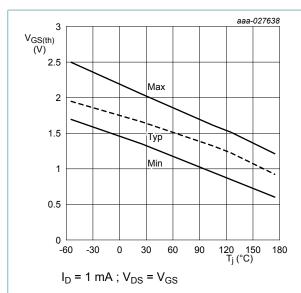


Fig. 10. Gate-source threshold voltage as a function of junction temperature

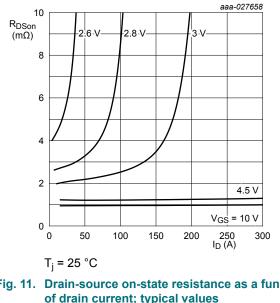


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

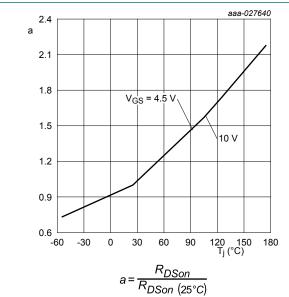


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

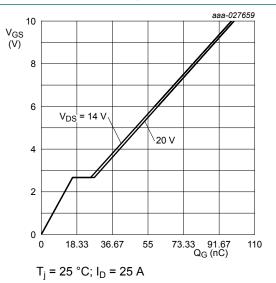


Fig. 13. Gate-source voltage as a function of gate charge; typical values

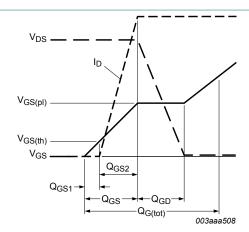
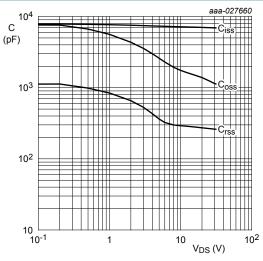


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

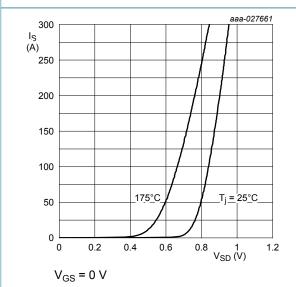
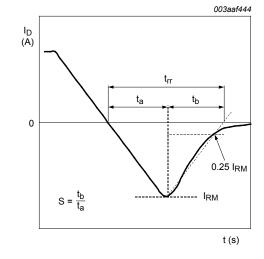


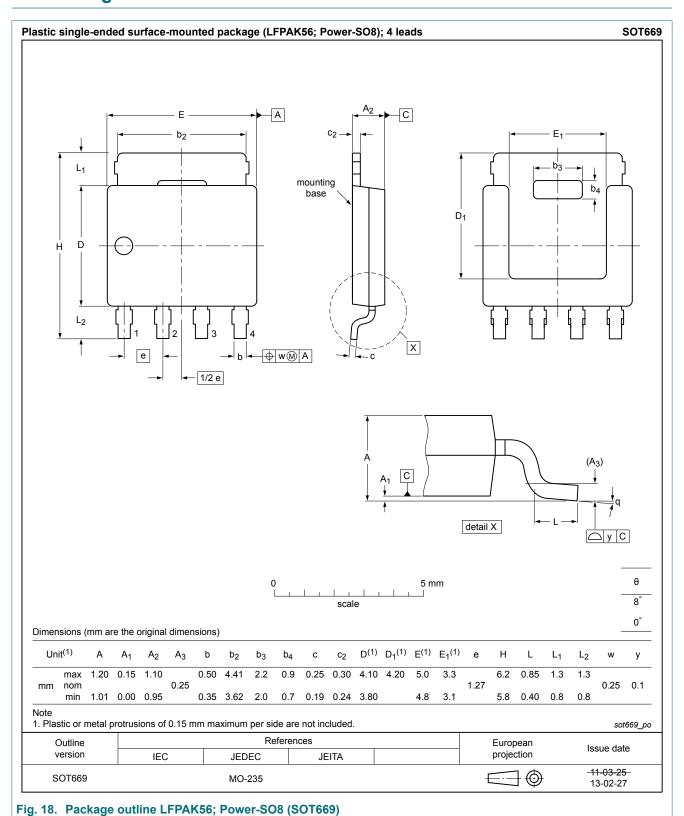
Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values



 $t_{rr} = t_a + t_b$

Fig. 17. Reverse recovery waveform definitions

11. Package outline



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